



## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#111/C  
7/13/01  
Sunder

Applicant(s): Park, et al.

Group Art Unit: 2814

Application No.: 09/173,129

Examiner: Peralta, G.

Filed: 10/15/1998

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, Washington, D.C. 20231 on 6/26/01.

Title: Selective Oxidation for Semiconductor Device Fabrication

Attorney Docket No.: TI-25320

Name

6/26/01

Date

Commissioner for Patents

Washington, D.C. 20231

RECEIVED  
JUL 10 2001  
TECHNOLOGY CENTER 2600RESPONSE UNDER 37 CFR 1.111

Dear Sir:

In response to the Office Action of February 27, 2001, please amend this application as follows:

In the claims:

Please substitute each of the following claims for the pending claim of the same number:

- 1 (Thrice Amended). A method of fabricating, in a semiconductor processing chamber, an electrical device formed in a semiconductor substrate, said method comprising:
- forming an insulating layer over said semiconductor substrate;
  - forming a silicon-containing structure on said insulating layer;
  - forming a conductive structure on said silicon-containing structure; and
  - oxidizing a portion of said insulating layer and said silicon-containing structure